Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	,					
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, I}_{D} = 250 \mu\text{A}$	20			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		20.2		mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}$			- 2.75		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.45		0.95	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1	μΑ
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 85 °C			10	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	20			Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 4.6 \text{ A}$		0.041	0.049	Ω
		$V_{GS} = 2.5 \text{ V}, I_D = 4.3 \text{ A}$		0.047	0.056	
		V _{GS} = 1.8 V, I _D = 3.9 A		0.054	0.065	
Forward Transconductance	9 _{fs}	V _{DS} = 10 V, I _D = 4.6 A		15		mS
Dynamic ^b			•			•
Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		530		pF
Output Capacitance	C _{oss}			100		
Reverse Transfer Capacitance	C _{rss}			48		
Total Cata Charge	0	$V_{DS} = 10 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 4.6 \text{ A}$		6.6	10	pC
Total Gate Charge	Q_g			6	9	
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 4.6 \text{ A}$		1.5		
Gate-Drain Charge	Q_{gd}			0.9		
Gate Resistance	R_{g}	f = 1 MHz		7.3	11	Ω
Turn-On Delay Time	t _{d(on)}	$V_{DD} = 10 \text{ V, } R_L = 2.7 \Omega$ $I_D \cong 3.7 \text{ A, } V_{GEN} = 4.5 \text{ V, } R_g = 1 \Omega$		8.5	13	ns
Rise Time	t _r			45	68	
Turn-Off DelayTime	t _{d(off)}			35	53	
Fall Time	t _f			82	123	
Drain-Source Body Diode Characteristic	cs					
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			2.3	А
Pulse Diode Forward Current ^a	I _{SM}				20	
Body Diode Voltage	V _{SD}	I _S = 2.2 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 3.2 A, dI/dt = 100 A/μs		10.6	16	nC
Body Diode Reverse Recovery Charge	Q _{rr}			3.7	5.7	ns
Reverse Recovery Fall Time	t _a			6.2		
Reverse Recovery Rise Time	t _b			4.4		

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

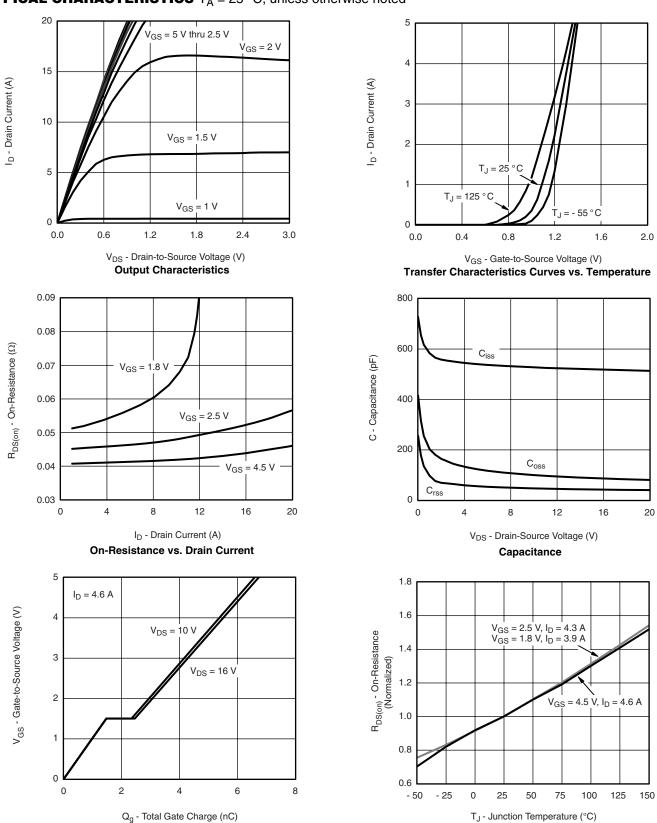
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted



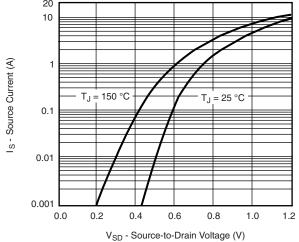
Gate Charge

On-Resistance vs. Junction Temperature

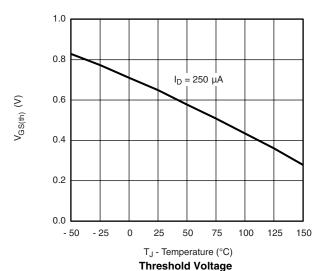
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TYPICAL CHARACTERISTICS $T_A = 25 \, ^{\circ}C$, unless otherwise noted

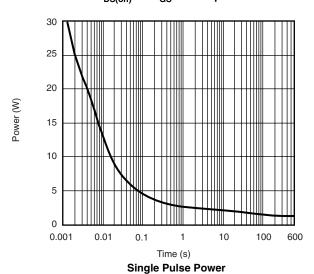


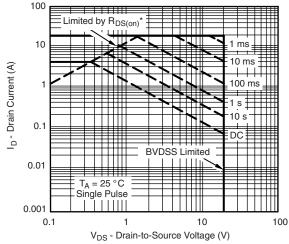
Source-Drain Diode Forward Voltage



 $C_{\text{S}} = 0.12$ $C_{\text{S}} = 0.09$ $C_{\text{S}} =$

 V_{GS} - Gate-to-Source Voltage (V) $\mathbf{R}_{DS(on)}$ vs. V_{GS} vs. Temperature





* $V_{GS} > \mbox{minimum } V_{GS}$ at which $R_{DS(on)}$ is specified

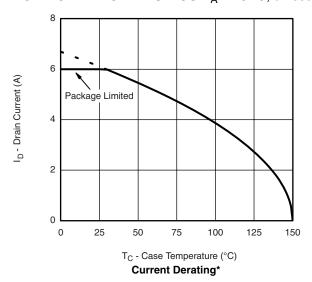
Safe Operating Area, Junction-to-Ambient

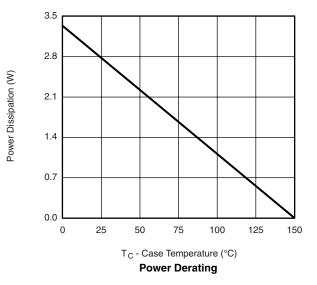






TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted



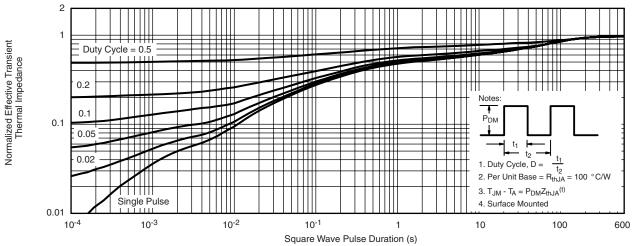


^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

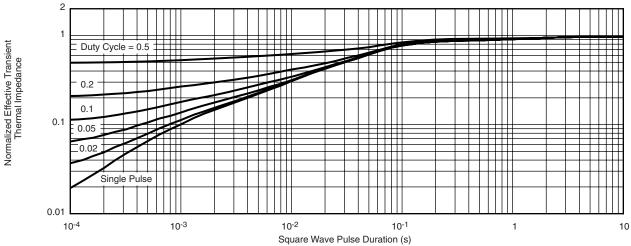
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TYPICAL CHARACTERISTICS $T_A = 25 \, ^{\circ}C$, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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